

Applicant: Toshiki Makimoto, et al.

Confirmation No.: 2860

Serial No.: 10/516,380

Att'y Docket No.: 14321.63

Filing Date: November 30, 2004

Art Unit: 2818

For: P-TYPE NITRIDE SEMICONDUCTOR STRUCTURE AND BIPOLAR TRANSISTOR

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Examiner <u>Initial*</u>	Document <u>Number</u>	Issue <u>Date</u>	<u>Name</u>
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Foreign Patent Documents

Examiner <u>Initial*</u>	Document <u>Number</u>	Publication <u>Date</u>	Country or <u>Patent Office</u>	<u>Translation</u>
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Other Documents

(including author, title, pertinent pages, etc.)

Examiner
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- _____ 1 T. Makimoto, et al., *High Current Gains Obtained by InGaN/GaN Double Heterojunction Bipolar Transistors with P-InGaN Base*, Applied Physics Letters, 79, No. 3, pp. 380-381, July 16, 2001.
- _____ 2 Supplementary European Search Report of related European Application No. 04700296.9, dated April 6, 2009 (2 pages).

References Cited by Applicants

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The reference designations "A1," "A2," etc. (referring to Applicant's reference 1, Applicant's reference 2, etc.) will be used by the Examiner in the same manner as Examiner's reference designations "A," "B," "C," etc. on Office Action Form PTO-1142.

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